

# EH1420SJETS-2.000M TR



## ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc J-Lead 9.8mm x 14.0mm Plastic Surface Mount (SMD) 2.000MHz  $\pm 20$ ppm  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$

## ELECTRICAL SPECIFICATIONS

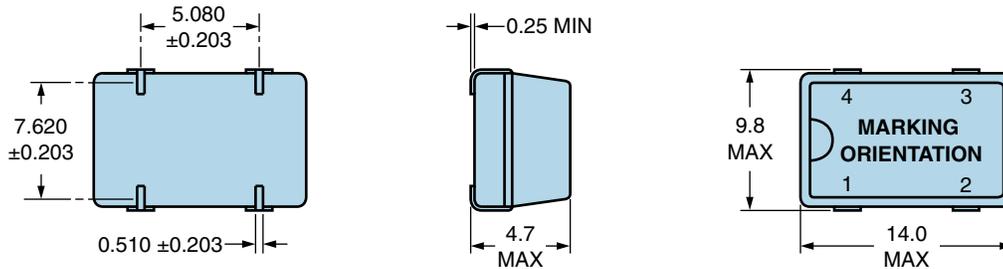
Nominal Frequency	2.000MHz
Frequency Tolerance/Stability	$\pm 20$ ppm Maximum (Inclusive of all conditions: Calibration Tolerance at $25^{\circ}\text{C}$ , Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at $25^{\circ}\text{C}$ , Shock, and Vibration)
Aging at $25^{\circ}\text{C}$	$\pm 5$ ppm/year Maximum
Operating Temperature Range	$-40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$
Supply Voltage	5.0Vdc $\pm 10\%$
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load, IOH = -16mA
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load, IOL = +16mA
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 $\pm 10$ (%) (Measured at 1.4Vdc with TTL Load or at 50% of waveform with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (Disabled Output: High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	$\pm 250$ pSec Maximum, $\pm 100$ pSec Typical
One Sigma Clock Period Jitter	$\pm 50$ pSec Maximum, $\pm 30$ pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	$-55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$

## ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A (Internal Crystal Only)
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C (Internal Crystal Only)
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Moisture Resistance	MIL-STD-883, Method 1004
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

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## MECHANICAL DIMENSIONS (all dimensions in millimeters)

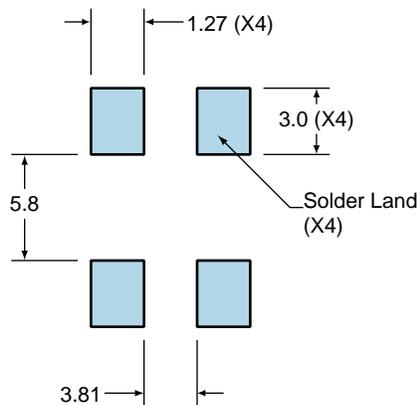


PIN	CONNECTION
1	Tri-State (High Impedance)
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	<b>ECLIPTEK</b>
2	<b>2.0000M</b>
3	<b>XXXXX</b> XXXXX=Ecliptek Manufacturing Identifier

## Suggested Solder Pad Layout

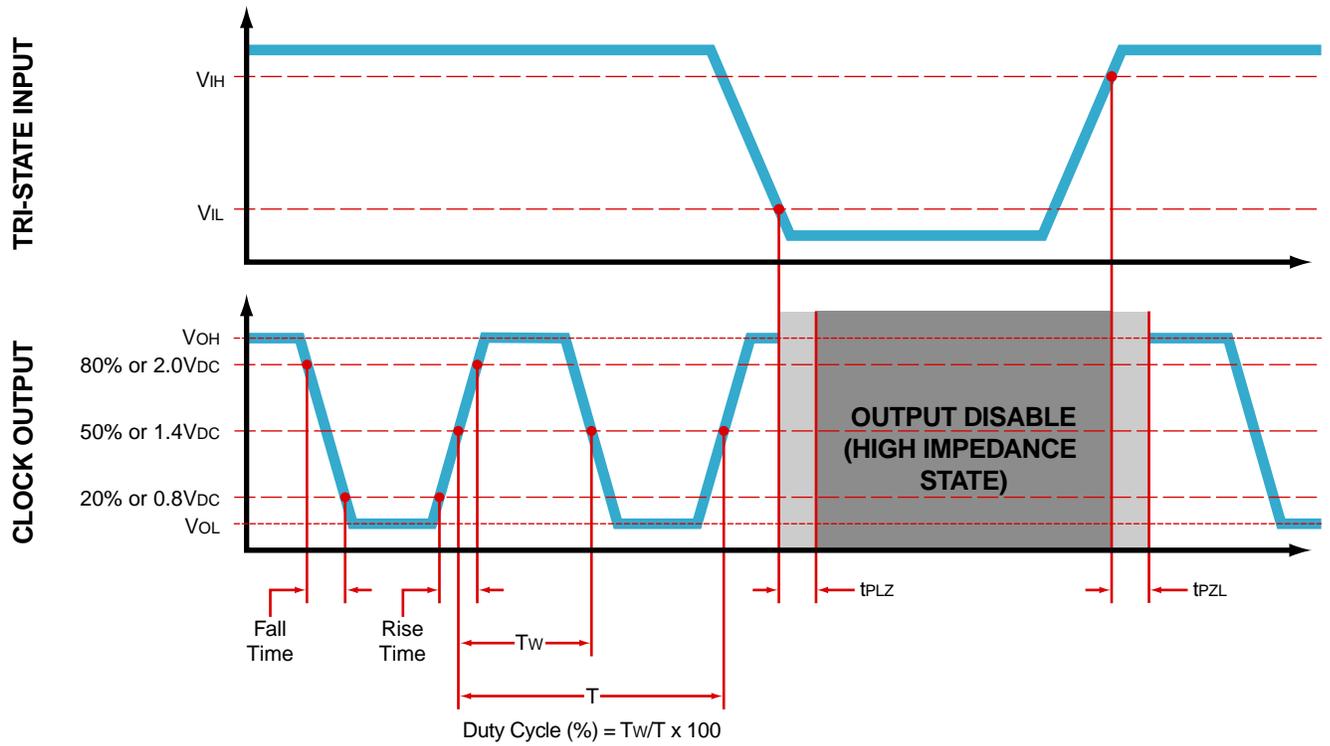
All Dimensions in Millimeters



All Tolerances are  $\pm 0.1$

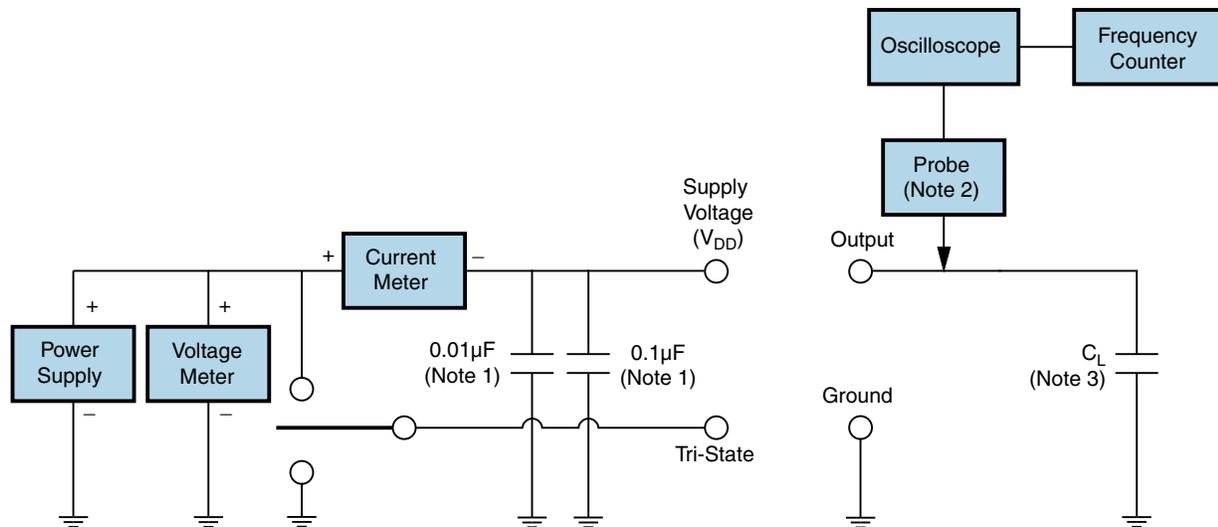
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## OUTPUT WAVEFORM & TIMING DIAGRAM



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## Test Circuit for CMOS Output



Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

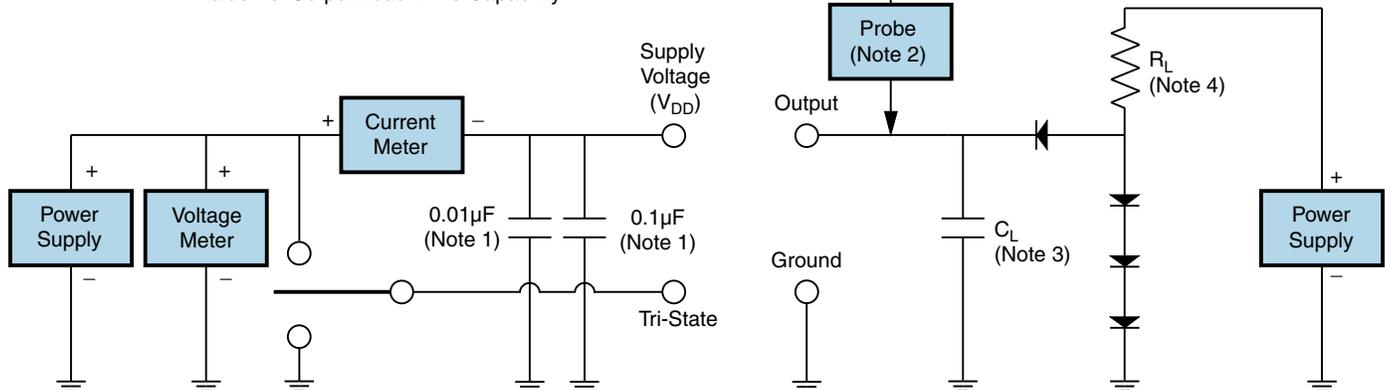
Note 3: Capacitance value C<sub>L</sub> includes sum of all probe and fixture capacitance.

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## Test Circuit for TTL Output

Output Load Drive Capability	$R_L$ Value (Ohms)	$C_L$ Value (pF)
10TTL	390	15
5TTL	780	15

Table 1:  $R_L$  Resistance Value and  $C_L$  Capacitance Value Vs. Output Load Drive Capability



Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value  $R_L$  is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

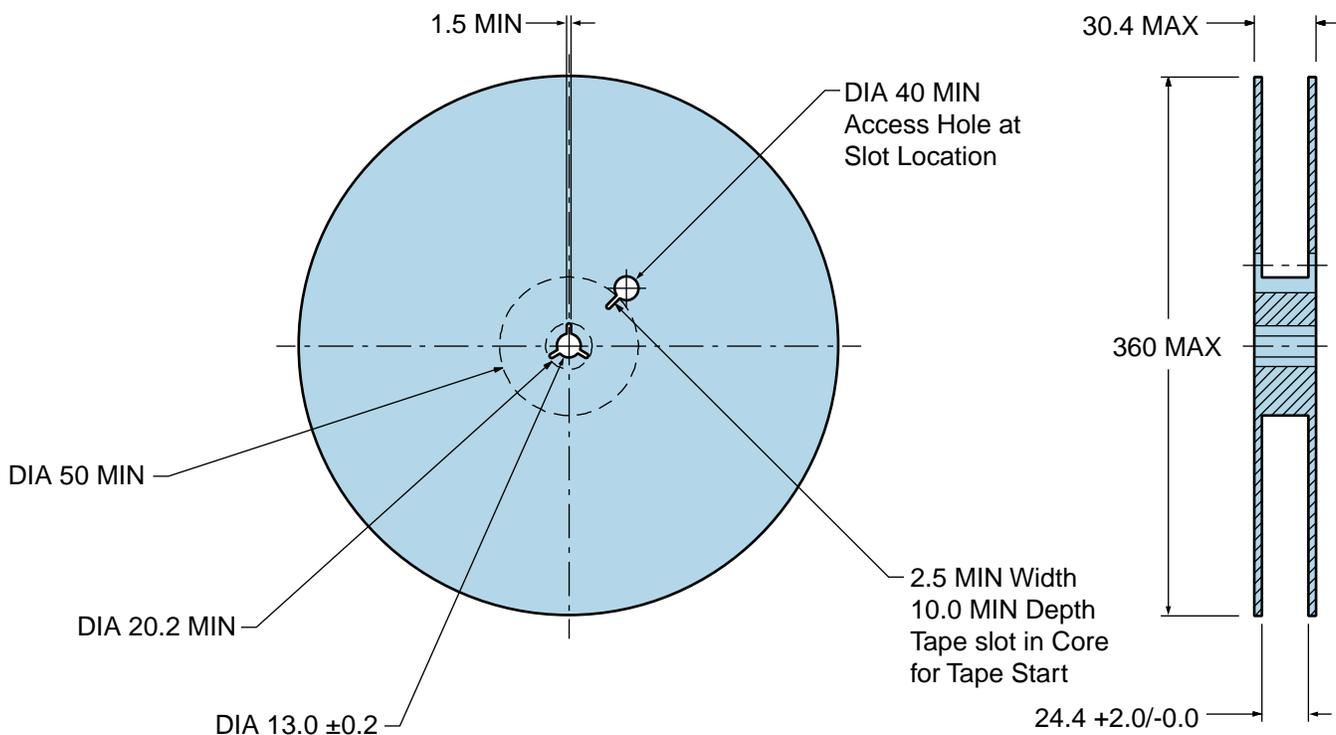
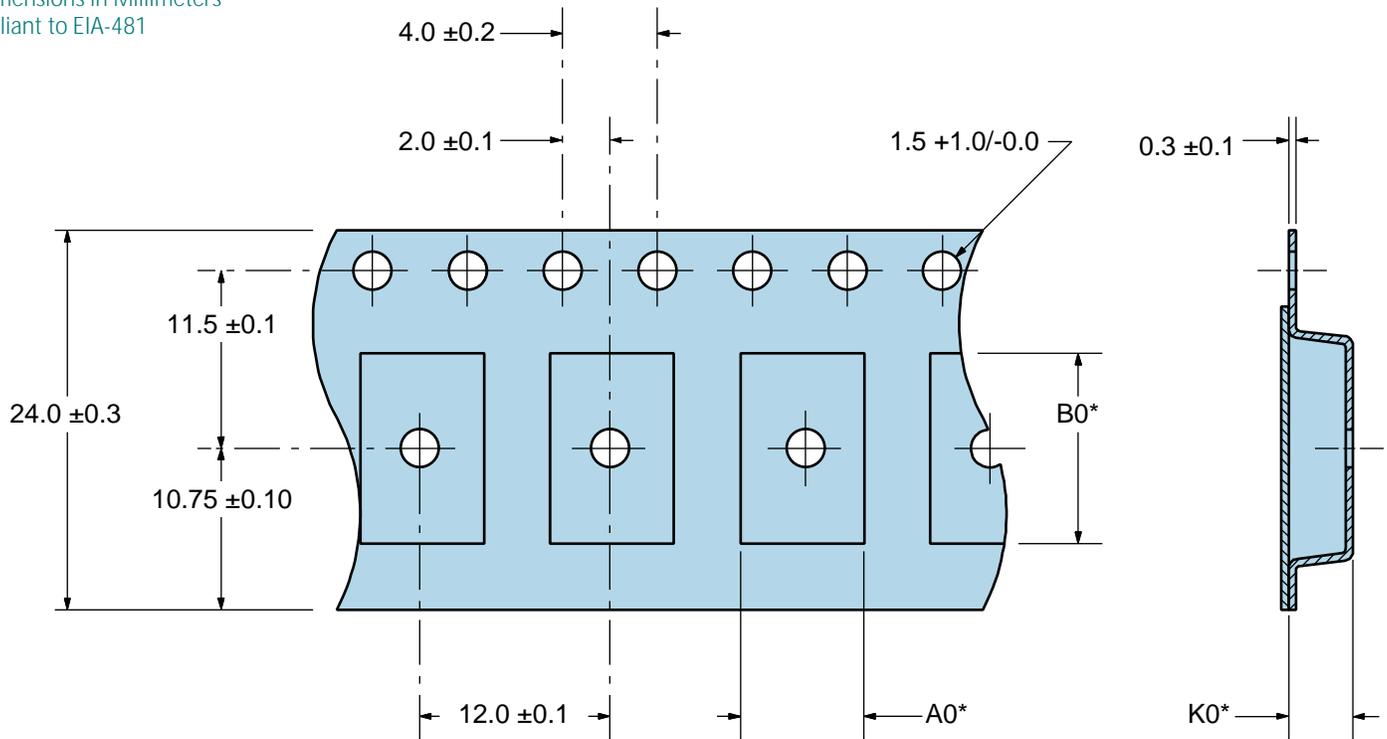
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## Tape & Reel Dimensions

Quantity Per Reel: 1,000 units

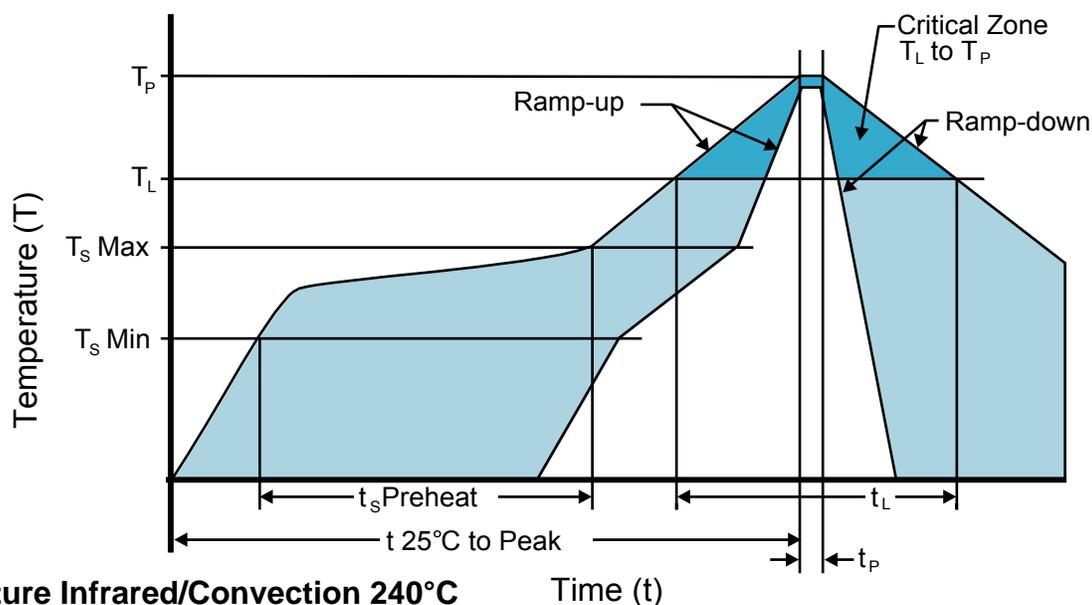
All Dimensions in Millimeters

Compliant to EIA-481



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## Recommended Solder Reflow Methods



### Low Temperature Infrared/Convection 240°C

$T_S$  MAX to  $T_L$  (Ramp-up Rate) 5°C/Second Maximum

#### Preheat

- Temperature Minimum ( $T_S$  MIN) N/A  
 - Temperature Typical ( $T_S$  TYP) 150°C  
 - Temperature Maximum ( $T_S$  MAX) N/A  
 - Time ( $t_s$  MIN) 60 - 120 Seconds

Ramp-up Rate ( $T_L$  to  $T_P$ ) 5°C/Second Maximum

#### Time Maintained Above:

- Temperature ( $T_L$ ) 150°C  
 - Time ( $t_L$ ) 200 Seconds Maximum

Peak Temperature ( $T_P$ ) 240°C Maximum

Target Peak Temperature ( $T_P$  Target) 240°C Maximum 2 Times / 230°C Maximum 1 Time

Time within 5°C of actual peak ( $t_p$ ) 10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time

Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

### Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum.

### High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum.